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4. (Amended) A method for fabricating a silicide for a silicon region, said method comprising:
- depositing a metal containing silicon or an alloy thereof on a bulk silicon substrate;
 - reacting said metal containing silicon or said alloy to form a first silicide phase;
 - etching any unreacted metal containing silicon or alloy;
 - depositing a silicon cap layer over said first silicide phase;
 - reacting the silicon cap layer to form a second silicide phase; and
 - etching any unreacted silicon from said silicon cap layer.

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8. (Amended) The method of claim 4, wherein said reacting of said metal comprises performing a first rapid thermal anneal (RTA) to form a metal-silicon phase, such that the deposited metal containing silicon with the underlay Si, converts some of the Si into metal-Si,
- wherein said etching comprises selectively etching any unreacted metal containing silicon, thereby leaving the metal-silicon regions intact,
- wherein said depositing comprises performing a blanket deposition of a silicon film, and
- wherein said reacting of said silicon cap comprises performing a second RTA to form a metal di-silicide.

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10. (Amended) A method for fabricating a silicide for a silicon region, said method comprising:
- depositing a metal or an alloy thereof on a bulk silicon substrate;
 - reacting said metal or said alloy to form a first silicide phase;
 - etching any unreacted metal or alloy;
 - depositing a silicon cap layer over said first silicide phase;
 - reacting the silicon cap layer to form a second silicide phase; and
 - etching any unreacted silicon from said silicon cap layer,
- wherein said metal is co-deposited with silicon.

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13. (Amended) A method for fabricating a silicide, said method comprising:
providing a substrate having a silicon layer;
depositing a metal containing silicon or an alloy over said silicon layer;
reacting said metal containing silicon or said alloy to form a first silicide phase;
etching any unreacted metal containing silicon or alloy; and
depositing a silicon cap layer over said metal containing silicon or said alloy;
reacting the silicon cap layer, to form a second silicide phase; and
etching any unreacted silicon from said silicon cap layer.

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25. (Amended) A method for fabricating a silicide for a semiconductor device, said method comprising:
depositing a metal or an alloy thereof on a silicon substrate;
reacting said metal or said alloy to form a first forming silicide phase;
etching any unreacted metal or alloy;
depositing a silicon cap layer over said first forming silicide phase;
reacting the silicon cap layer to form a second silicide phase, for said semiconductor device; and
etching any unreacted silicon from said silicon cap layer.

26. (Amended) A method for fabricating a silicide for a silicon region, said method comprising:
depositing a metal containing silicon or an alloy thereof on a bulk silicon substrate;
reacting said metal containing silicon or said alloy to form a first silicide phase;
etching any unreacted metal containing silicon or alloy;
depositing a silicon cap layer over said first silicide phase;
reacting the silicon cap layer to form a second phase; and
etching any unreacted silicon from said silicon cap layer, wherein said metal is nickel.